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			U.S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2 (if known)</sup>			
JWC		US-2003/0067045 A1	04-10-2003	Sugiyama et al.	
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		FOREIG	N PATENT DOCU	IMENTS		
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NON PATENT LITERATURE DOCUMENTS					
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SWL		GHANI, T. et al., "100 nm Gate Length High Performance/Low Power CMOS Transistor Structure," IEDM (1999) pp. 415-418.			
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Signature	CRANE	Considered	11/2003

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